

Study of Buried Waveguide Written in LiNbO₃ Crystal by High Repetition Rate Femtosecond Laser

Fan Zongxue Feng Jie Liu Ang Yang Yongjia Zhou Zigang

School of Science, Southwest University of Science and Technology, Mianyang, Sichuan 621010, China

Abstract A buried waveguide in LiNbO₃ crystal is fabricated, by using the femtosecond laser which repetition rate is 25 MHz. The etching region can be divided into two regions which are inner interaction region and thermally modified region respectively. The coupling experiment shows two single mode buried waveguides are generated in the thermally modified region, and the propagation loss of the two waveguides are below 1.5 dB/cm. At the same time, the inner interaction region leading to a low transmittance. The Raman spectrum of the etching region is measured which shows the light-guide region is densificated by the thermal effect of high repetition, and there is a large-scale defects in the inner interaction region.

Key words laser optics; femtosecond laser; waveguide; Raman scattering; LiNbO₃

OCIS codes 140.6810; 230.7380; 140.7090

高重复频率飞秒激光刻写铌酸锂光波导的研究

范宗学 冯杰 刘昂 杨永佳 周自刚

西南科技大学理学院, 四川 绵阳 621010

摘要 利用重复频率为 25 MHz 的飞秒激光刻写铌酸锂掩埋式光波导,研究了在激光作用中心及热影响区域的物质结构,采用 650 nm 的激光进行端面耦合实验,观测刻写区域波导的光传输特性及损耗测量。研究发现,在激光刻写区域的上下两个部位分别形成了传输损耗低于 1.5 dB/cm 的单模光波导,而刻写区域中心未形成波导结构且光传输性能较弱。拉曼分析显示,刻写区域上下两个部位形成了致密化波导结构,而刻写中心形成了大尺度的缺陷。

关键词 激光光学; 飞秒激光; 光波导; 拉曼; 铌酸锂

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1 Introduction

LiNbO₃ is one of the most widely used dielectric materials in photonics and optoelectronics due to its excellent nonlinear optical, electro-optical, acousto-optical, piezoelectric and photorefractive properties^[1]. In many of these applications, compact active components are required that can form into optical waveguides, integrated optical circuits, and other light control systems. LiNbO₃ waveguide fabrication processes must induce positive refractive index changes. Several methods such as metallic elements diffusion, ion implantation and proton exchange have put forward to fabricate low-loss channel waveguides^[2-5]. However, these methods still involve complex multi-step procedures that degrade the LiNbO₃ properties in some cases^[6-7], and all these methods are limited to forming only near-surface waveguide structures. In recent years, direct laser writing has emerged as a unique and flexible method for the fabrication of three dimensional integrated optical devices^[8-10]. Buried waveguides are formed by the focused femtosecond laser beam with induce nonlinear absorption in LiNbO₃ crystals^[10-19].

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作者简介: 范宗学(1990—),男,硕士研究生,主要从事飞秒激光微纳加工方面的研究。E-mail: 1596561081@qq.com

导师简介: 周自刚(1973—),男,教授,主要从事集成光学与微小光学器件方面的研究。E-mail: zhouzigang1973@163.com

Early researches of laser-writing waveguide in LiNbO_3 were focused on low-repetition rate (1~5 kHz) femtosecond lasers^[10,12-13]. Recently, high-repetition rate femtosecond lasers have been applied over a broader multidimensional parameter space for optimizing optical loss, mode symmetry, and processing speed^[11,19]. Although there are many studies on laser-writing waveguide in LiNbO_3 , there is seldom report about the photo-physical and photochemical mechanisms responsible for the formation of this laser-induced optical waveguide, and the micro-structural lattice modifications underlying the positive refractive index change. A clear association of the LiNbO_3 lattice modifications with the waveguide characteristics together with a detailed morphological characterization would provide fundamental understanding of the processes as well as insights into better controlling the waveguide properties, functionality, and stability that are necessary to broaden the range of LiNbO_3 photonic applications.

In this paper, the buried waveguide in LiNbO_3 crystal by the 25 MHz repetition femtosecond laser is fabricated, and then performed the coupling experiment to study the characteristics of the waveguides, Raman scattering measurements is performed at different regions of the cross section of the etching region to study the mechanism of LiNbO_3 waveguide induced by high repetition rate femtosecond laser.

2 Experiment

For the fabrication of the waveguides, an amplified Ti: sapphire laser system with central wavelength of 800 nm is used, 25 MHz repetition rate, average output power was 540 mW, and pulse duration about 100 fs. The sample was mounted upon a computer-controlled three-axis positioning system. The laser pulses were focused into a polished LiNbO_3 sample by a 40× microscope objective which numerical aperture (NA) is 0.65. Waveguides was fabricated by using a single translational scan along the x direction at the speed of 10 mm/s. A schematic of the setup is given in Fig.1.

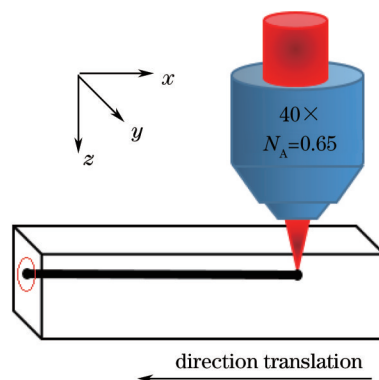


Fig.1 Scheme of the writing process in LiNbO_3 crystal using fs laser pulses

Figure 2 shows the microscopic image of the waveguide. The laser modification zone in Fig. 2 (a) extends to 20 μm width, and the bright white color zone extends to 11 μm , greatly exceeding the 2 μm beam diameter

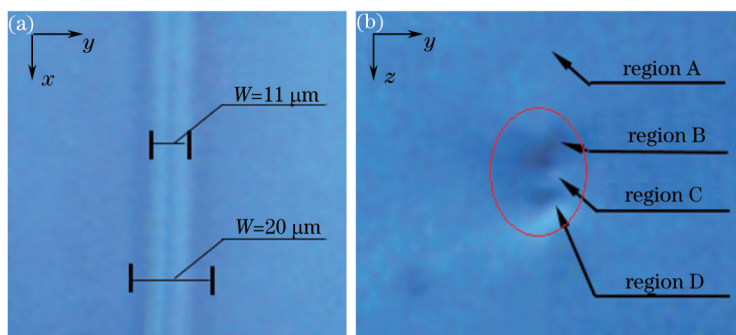


Fig.2 Microscopic image of femtosecond laser induced structure change in LiNbO_3 .

(a)Top view of the waveguide and (b) cross section of the waveguide

due to the heat accumulation effect^[20]. Figure 2 (b) shows the cross section of the waveguide, which including three regions (B, C, D), and the diameter of region B and region D is about 9 μm .

For the coupling experiment, the laser, as light source, which wavelength was 650 nm, the laser beam diagnostics as receptor, and using a nine-dimensional adjustment bracket to adjust the position of the sample, make sure the laser was coupled precision with the waveguide. Measuring the light intensity distribution of the laser that transmitted through waveguide, and the results are shown in follow Figs.3 (a)~(c).

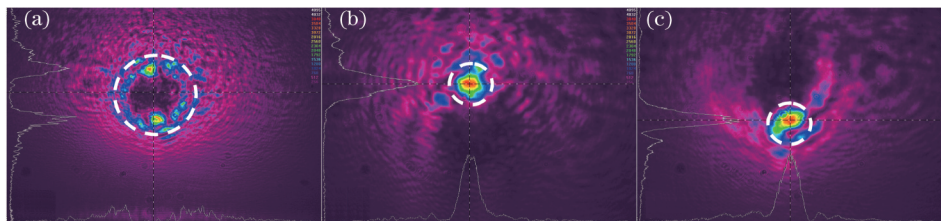


Fig.3 Light intensity distribution, the near-field map of 650 nm light guided within the three different regions of the waveguide. (a) Light intensity distribution of the whole region induced by fs laser, (b) region B and (c) shows the region D

According to Fig.3 (a), the light of region C was weakness, therefore, the transmittance of this region is lower, and region C does not possess the characteristics of optical waveguide, and neither does the annular region outside of region C (except region B and D, with those regions have light transmitted). However, according to Fig.3 (b) and (c), region B and region D have the characteristics of optical waveguide, the light intensity of region B and D are approximately to Gaussian distribution. With the light intensity distribution and the size of region B and D, it is concluded that the regions B, D generated a single mode waveguide^[21]. The experiment of propagation loss in two waveguides show that the region B was 1.2 dB/cm at 650 nm, and 0.9 dB/cm in region D.

3 Analysis

For the study of the mechanism of the fabrication of waveguide in LiNbO_3 by high repetition rate femtosecond laser, Raman scattering measurements at the different regions of the cross section of the waveguide are performed, and the result is shown in Fig.4.

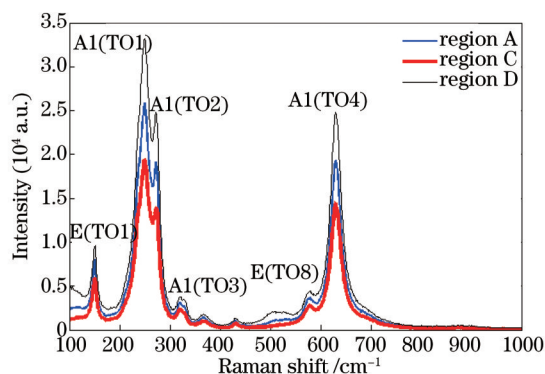


Fig.4 Typical micro-Raman spectra recorded from three regions of the LiNbO_3 sample and labeled with the six main phonon modes accessible for Raman configuration

Following the spectral classification of previous studies^[22], the main phonon modes accessible with this configuration are identified in the figure and summarized as follows table.1.

Table 1 Summary of the results obtained for the analyzed Raman modes and a short description of the characteristics of each one

Phonon mode	Description
A1(TO1)	Movement of the ions in Nb ⁵⁺ sites along the Z-axis direction and against the oxygen plane.
A1(TO2)	Displacement of ions in Nb ⁵⁺ and Li ⁺ sites along the Z-axis, oxygen remains motionless.
A1(TO3)	Deformation of the oxygen octahedron in the XY plane.
A1(TO4)	Deformation of the oxygen octahedron in the XY plane.
E(TO1)	Nb ⁵⁺ /O vibrations in the XY plane.
E(TO8)	Deformation of the oxygen octahedron.

The previous studies indicates that A1 (TO4) mode corresponds to distortions of the oxygen octahedron only, along the x - y plane, and responds with much higher sensitivity to change the volume of the LiNbO₃ unit cell than the other phonon modes of LiNbO₃^[22]. Local densification and existence of compressive stress would cause phonon mode intensity at all Raman modes increase, and stronger for A1 (TO4)^[23]. Therefore, this mode is high relevance in assessing the compaction, and hences the refractive index changes, that is laser-induced in the LiNbO₃. From Fig.4 the Raman intensity of waveguide region D is more stronger than unmodified region A, and the A1 (TO1) mode increases more. Therefore, region D is mainly caused by densification and existence stress. However, the presence of large-scale defects would cause reduction in the overall Raman intensity^[24]. From Fig.4 the Raman intensity of center region C is weaker than unmodified region A, and from Fig.3 the region C has a little bit of transmission light, thus, the center region forms a large-scale defects which induced by femtosecond laser leading to low transmittance.

From the above analysis it is suggested that: the center of etching region (region C) is ablated by the high temperature due to the thermal effect of 25 MHz femtosecond laser interaction with LiNbO₃, and caused a large-scale defect for the performance of light transmittance reduced significantly in this region. However, regions B and D far from center region with densified structure induced by the force of heat flux, and formed waveguide in those regions.

4 Conclusion

In conclusion, by using tightly focused 25 MHz femtosecond laser to etch LiNbO₃ crystal, at the scanning speed of 10 mm/s, two buried single waveguides are generated in the top and below of the etching region, and which separated about 10 μm, the propagation loss of the two waveguides are below 1.5 dB/cm at 650 nm, however, waveguide could not be generated in the etching center, and the light transmission of this region significantly reduced. In general, low propagation waveguide can be fabricated in LiNbO₃ by high repetition femtosecond laser and lower plus energy or faster scanning speed may optimize its properties.

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